

FDS9412

Single N-Channel Enhancement Mode Field Effect Transistor

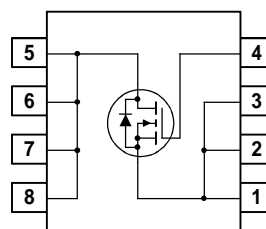
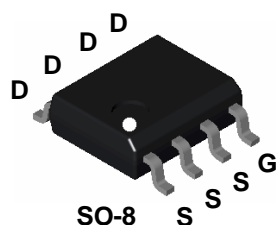
General Description

This N-Channel Logic Level MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

These devices are particularly suited for low voltage applications such as notebook computer DC-DC converter where fast switching, low conduction loss and high efficiency are needed.

Features

- 7.9 A, 30 V. $R_{DS(ON)} = 22\text{ m}\Omega$ @ $V_{GS} = 10\text{ V}$
 $R_{DS(ON)} = 36\text{ m}\Omega$ @ $V_{GS} = 4.5\text{ V}$
- Very low gate charge.
- High switching speed
- High performance trench technology for extremely low $R_{DS(ON)}$
- High power and current handling capability in a widely used surface mount package.



Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain-Source Voltage	30	V
V_{GSS}	Gate-Source Voltage	± 20	V
I_D	Drain Current – Continuous (Note 1a)	7.9	A
	– Pulsed	24	
P_D	Power Dissipation for Single Operation (Note 1a) (Note 1b) (Note 1c)	2.5	W
		1.2	
		1.0	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	50	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	25	$^\circ\text{C/W}$

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDS9412	FDS9412	13"	12mm	2500 units

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain–Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, Referenced to 25°C		28		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}$			1	μA
I_{GSSF}	Gate–Body Leakage, Forward	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$			100	nA
I_{GSSR}	Gate–Body Leakage, Reverse	$V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$			-100	nA

On Characteristics (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1	1.6	2.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, Referenced to 25°C		-4.3		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain–Source On–Resistance	$V_{GS} = 10\text{ V}, I_D = 7.9\text{ A}$ $V_{GS} = 10\text{ V}, I_D = 7.9\text{ A}, T_J = 125^\circ\text{C}$ $V_{GS} = 4.5\text{ V}, I_D = 6.2\text{ A}$		19 30 25	22 35 36	m Ω
$I_{D(on)}$	On–State Drain Current	$V_{GS} = 10\text{ V}, V_{DS} = 5\text{ V}$	16			A
g_{FS}	Forward Transconductance	$V_{DS} = 10\text{ V}, I_D = 7.9\text{ A}$		22		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$		830		pF
C_{oss}	Output Capacitance			185		pF
C_{rss}	Reverse Transfer Capacitance			80		pF

Switching Characteristics (Note 2)

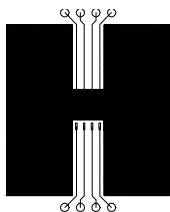
$t_{d(on)}$	Turn–On Delay Time	$V_{DD} = 10\text{ V}, I_D = 1\text{ A},$ $V_{GS} = 10\text{ V}, R_{GEN} = 6\text{ }\Omega$		6	12	ns
t_r	Turn–On Rise Time			10	20	ns
$t_{d(off)}$	Turn–Off Delay Time			18	32	ns
t_f	Turn–Off Fall Time			5	10	ns
Q_g	Total Gate Charge	$V_{DS} = 12\text{ V}, I_D = 7.9\text{ A},$ $V_{GS} = 10\text{ V}$		14	22	nC
Q_{gs}	Gate–Source Charge			2.7		nC
Q_{gd}	Gate–Drain Charge			3.0		nC

Drain–Source Diode Characteristics and Maximum Ratings

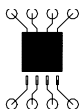
I _S	Maximum Continuous Drain–Source Diode Forward Current				2	A
V _{SD}	Drain–Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 2 A (Note 2)		0.7	1.2	V

Notes:

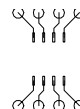
1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 50°W when mounted on a 1 in^2 pad of 2 oz copper



b) 105°W when mounted on a $.04\text{ in}^2$ pad of 2 oz copper



c) 125°W when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width $< 300\text{ }\mu\text{s}$, Duty Cycle $< 2.0\%$

Typical Characteristics

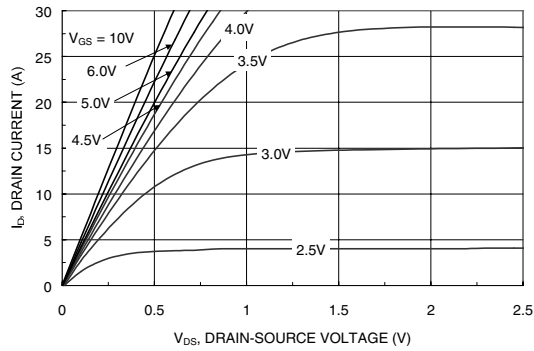


Figure 1. On-Region Characteristics.

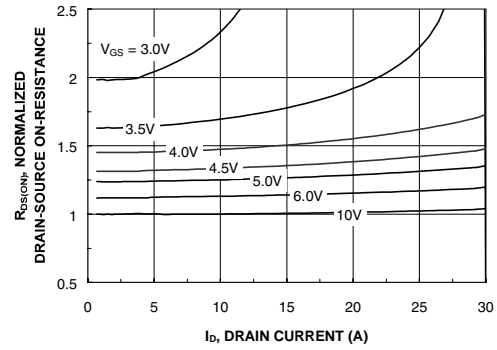


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

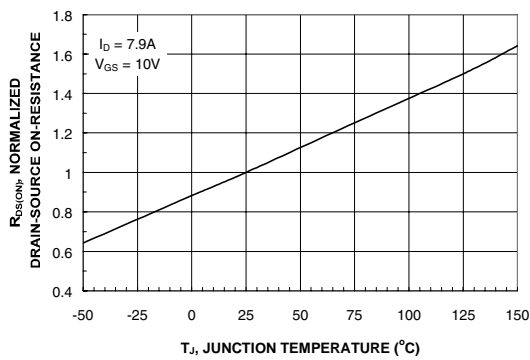


Figure 3. On-Resistance Variation with Temperature.

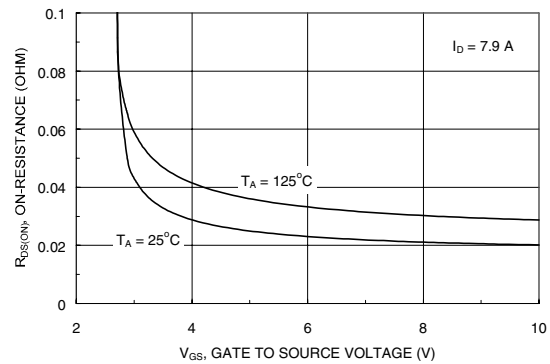


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

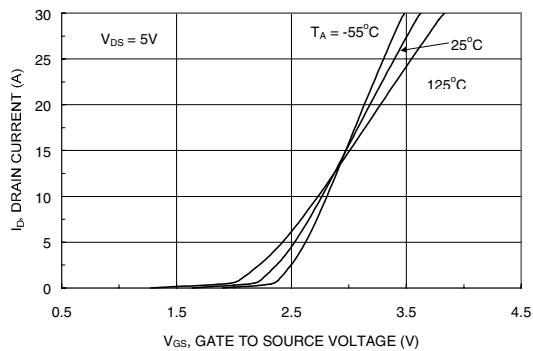


Figure 5. Transfer Characteristics.

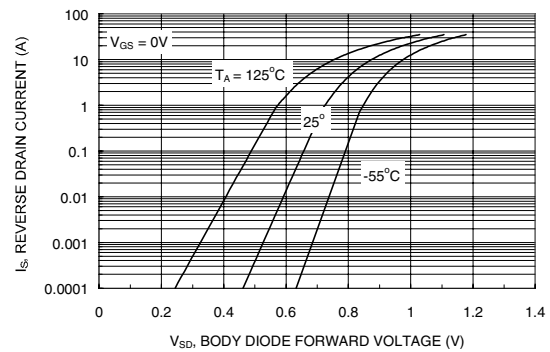


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

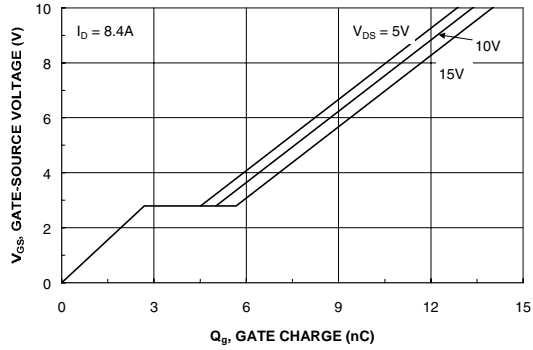


Figure 7. Gate Charge Characteristics.

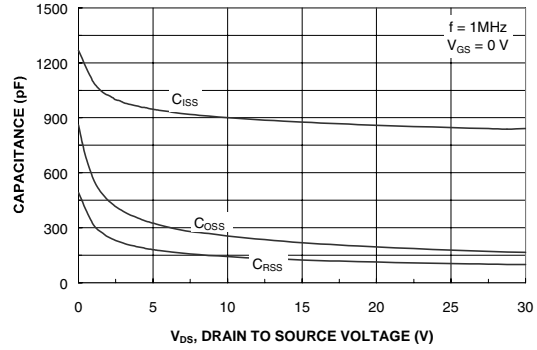


Figure 8. Capacitance Characteristics.

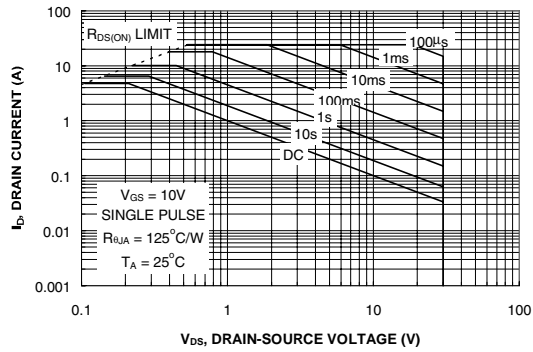


Figure 9. Maximum Safe Operating Area.

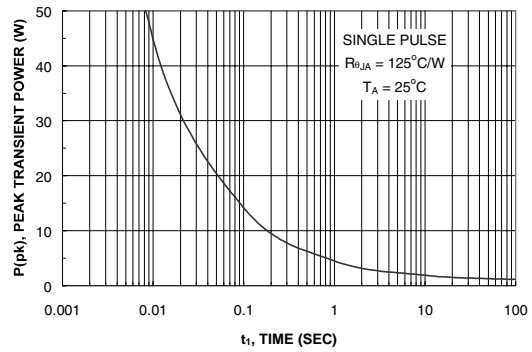


Figure 10. Single Pulse Maximum Power Dissipation.

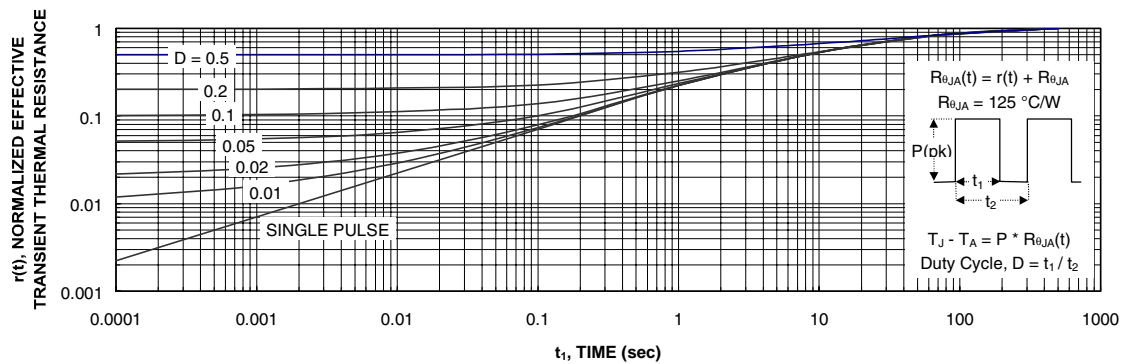


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c.
Transient thermal response will change depending on the circuit board design.